

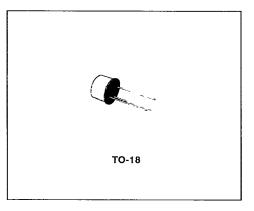
T-27-04 BCY70 BCY71/BCY72

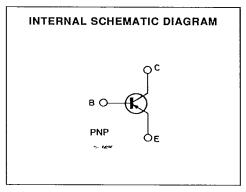
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GENERAL PURPOSE APPLICATIONS

DESCRIPTION

The BCY70, BCY71 and BCY72 are silicon planar epitaxial PNP transistors in Jedec TO-18 metal case.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		11		
		BCY70	BCY71	BCY72	Unit
V _{CBO}	Collector-base Voltage (I _E = 0)	- 50	- 45	- 25	V
VCEO	Collector-emitter Voltage (I _B = 0)	- 40	- 45	- 25	V
VEBO	Emitter-base Voltage (I _C = 0)	- 5			V
Iсм	Collector Peak Current	- 200			mA
Ptot	Total Power Dissipation at Tamb ≤ 25 °C	350			mW
T _{stg} , T _j	Storage and Junction Temperature	- 65 to 200		°C	

Pulsed : pulse duration = 300 µs, duty cycle = 1 %.

October 1988

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Rth incase Max		
R _{th i-case} Thermal Resistance Junction-case Max	150	°C/W
Rth j-amb Thermal Resistance Junction-ambient Max	500	°C/W

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25 \ ^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
ICES	Collector Cutoff Current (V _{BE} = 0)	For BCY70 $V_{CE} = -20 V$ $V_{CE} = -50 V$ For BCY71 $V_{CB} = -20 V$ $V_{OB} = -45 V$ For BCY72 $V_{CB} = -20 V$ $V_{CB} = -20 V$			- 10 - 500 - 100 - 10 - 100 - 10	nA nA nA μA nA μA
I _{EBO}	Emitter cutoff Current (I _C = 0)	V _{EB} = - 5 V			- 10	μA
V _{CE(sat)} *	Collector-emitter Saturation Voltage	$I_{C} = -10 \text{ mA}$ $I_{B} = -1 \text{ mA}$ $I_{C} = -50 \text{ mA}$ $I_{B} = -5 \text{ mA}$			- 0.25 - 0.5	V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	$ \begin{array}{ll} I_C = - \ 10 \ \text{mA} & I_B = - \ 1 \ \text{mA} \\ \text{For } \textbf{BCY70} \ \text{and} \ \textbf{BCY71} \ \text{Only} \\ I_C = - \ 50 \ \text{mA} & I_B = - \ 5 \ \text{mA} \end{array} $	- 0.6		0.9 1.2	v v
h _{FE} *	DC Current Gain	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	40 45 50 15 80 90 100 15 40 50	60	600	
h _{fe}	Small Signal Current Gain (for BCY71 only)	I _C = - 1 mA V _{CE} = - 10 V f = 1 kHz	100		400	
fT	Transition Frequency		15 250 200	-		MHz MHz MHz
СЕВО	Emitter-base Capacitance	I _C = 0 V _{EB} = 1 V f = 1 MHz			8	pF
Ссво	Collector-base Capacitance	I _E = 0 V _{CB} = - 10 V f = 1 MHz			6	pF

* Pulsed : pulse duration = 300 μs, duty cycle = 1 %.

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BCY70-BCY71-BCY72

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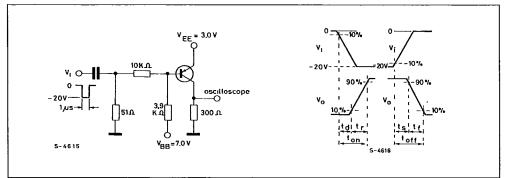
ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unlt
NF	Noise Figure				6	dB
		for BCY71			2	dB
hie	Input Impedance (for BCY71 only)	$I_{C} = -1 \text{ mA}$ $V_{CE} = -10 \text{ V}$ f = 1 kHz	2		12	kΩ
h _{re}	Reverse Voltage Ratio (for BCY71 only)	$I_{C} = -1 \text{ mA}$ $V_{CE} = -10 \text{ V}$ f = 1kHz			20x10 ⁻⁴	
h _{oe}	Output Admittance (for BCY71 only)	$l_{C} = -1 \text{ mA}$ $V_{CE} = -10 \text{ V}$ f = 1 kHz	10		60	μS
t _d	Delay Time (for BCY70 and BCY72 only)	$I_{C} = -10 \text{ mA}$ $V_{EE} = 3 \text{ V}$ $I_{B1} = -1 \text{ mA}$		23	35	ns
tr	Rise Time (for BCY70 and BCY72 only)	$I_{C} = -10 \text{ mA}$ $V_{EE} = 3 \text{ V}$ $I_{B1} = -1 \text{ mA}$		25	35	ns
ts	Storage Time (for BCY70 and BCY72 only)	$I_{C} = -10 \text{ mA}$ $V_{EE} = 3 \text{ V}$ $I_{B1} = -I_{B2} = -1 \text{ mA}$		270	350	ns
tf	Fall Time (for BCY70 and BCY72 only)	$I_{C} = -10 \text{ mA}$ $V_{EE} = 3 \text{ V}$ $I_{B1} = -I_{B2} = -1 \text{ mA}$		50	80	ns
ton	Turn-on Time (for BCY70 and BCY72 only)	$I_{C} = -10 \text{ mA}$ $V_{EE} = 3 \text{ V}$ $I_{B1} = -1 \text{ mA}$		48	65	ns
toff	Turn-off Time (for BCY70 and BCY72 only)	$I_{C} = -10 \text{ mA}$ $V_{EE} = 3 \text{ V}$ $I_{B1} = -I_{B2} = -1 \text{ mA}$		320	420	ns

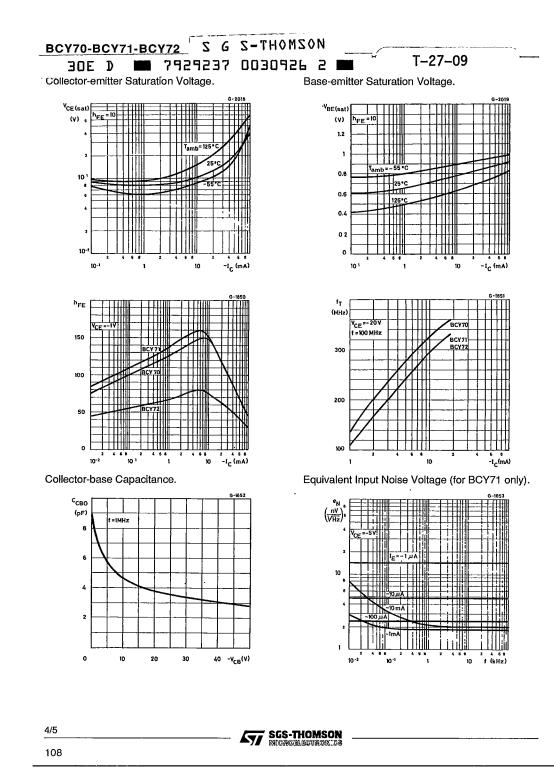
* Pulsed : pulse duration = 300 µs, duty cycle = 1 %.

TEST CIRCUIT

Test Circuit for Switching Times.







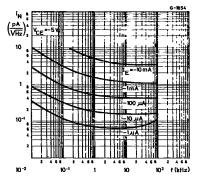
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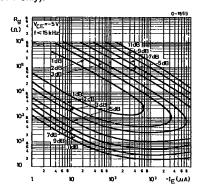
Equivalent Input Noise Current (for BCY71 only).



Countours of Constant White Noise Figure (for BCY71 only).

BCY70-BCY71-BCY72

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